11-1701

501.36931X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

pplicant(s):

IWASAKI, et al.

Serial No.:

09/255,856

Filed:

February 23, 1999

For:

SEMICONDUCTOR DEVICE WITH LAYERED

INTERCONNECT STRUCTURE

Group:

2813

Examiner:

S. Smoot

## **AMENDMENT**

Assistant Commissioner for Patents Washington, D.C. 20231

November 6, 2001

Sir:

In response to the Office Action mailed July 6, 2001, please amend the above-identified application as follows:

## **IN THE CLAIMS**

Please amend the claims presently in the application as follows:

1. (Twice Amended) A semiconductor device with a multilayered structure comprising a copper film interconnect formed on one primary surface of a semiconductor substrate, and a neighboring film formed in contact with said

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